

V _{RSM} V _{RRM}	I _{FRMS} (maximum values for continuous operations)					
	200 A		260 A		500 A	
	I _{FAV} (sin. 180; T _{case} = 100 °C)					
V	125 A	165 A	320 A			
400	SKN 100/04	SKR 100/04	SKN 130/04	SKR 130/04*	SKN 240/04	SKR 240/04*
800	100/08	100/08	130/08	130/08*	240/08	240/08*
1200	100/12	100/12	130/12	130/12*	240/12	240/12*
1400	100/14	100/14	130/14	130/14*	240/14	240/14*
1600	100/16	100/16	130/16	130/16*	240/16	240/16*
1800	100/18◆	100/18◆	130/18◆	130/18◆	240/18◆	240/18◆

Rectifier Diodes

SKN 100 SKR 100
SKN 130 SKR 130
SKN 240 SKR 240



Symbol	Conditions	SKN 100 SKR 100	SKN 130 SKR 130	SKN 240 SKR 240	Units
I _{FAV}	sin. 180; T _{case} = 100 °C = 125 °C	125 100	165 130	320 240	A
I _{FSM}	T _{vj} = 25 °C; 10 ms	1 750	2 500	6 000	A
i ² t	T _{vj} = 180 °C; 10 ms	1 500	2 000	5 000	A
	T _{vj} = 25 °C; 8,3 ... 10 ms	15 000	31 000	180 000	A ² s
	T _{vj} = 180 °C; 8,3 ... 10 ms	11 500	20 000	125 000	A ² s
Q _{rr}	T _{vj} = 160 °C; - di _F /dt = 10 A/μs	typ. 100	typ. 120	typ. 200	μC
I _R	T _{vj} = 25 °C; V _R = V _{RRM}	1	1	2	mA
	T _{vj} = 180 °C; V _R = V _{RRM}	15	22	60	mA
V _F	T _{vj} = 25 °C; (I _F = ...); max.	1,55 (400)	1,5 (500)	1,4 (750)	V
V _(TO)	T _{vj} = 180 °C	0,85	0,85	0,85	V
r _T	T _{vj} = 180 °C	1,8	1,3	0,6	mΩ
R _{thjc}		0,45	0,35	0,20	°C/W
R _{thch}		0,08	0,08	0,03	°C/W
T _{vj}		- 40 ... + 180		°C	
T _{stg}		- 55 ... + 180		°C	
M	SI units	10	30	Nm	
a	US units	90	270	lb.in.	
w	approx.	5 · 9,81	5 · 9,81	m/s ²	
		100	250	g	
RC	P _R = 2 W	0,25	0,25	0,5	μF
		50	50	30	Ω
R _p	P _R = 20 W	50	50	50	kΩ
Case		E 13	E 14	E 15	

Features

- Reverse voltages up to 1600 V
- Hermetic metal cases with glass insulators
- Threaded studs ISO M12, M16 x 1,5 (SKR 130 also 1/2 – 20 UNF or 3/8 – 24 UNF, SKR 240 also 3/4 – 16 UNF)
- **SKN:** anode to stud
- **SKR:** cathode to stud

Typical Applications

- All-purpose mean power rectifier diodes
- Cooling via heatsinks
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes

- ♦ available in limited quantities
- * available with UNF threads:
3/8 – 24 UNF 2 A (e.g. SKR 130/12 UNF 3/8) or
1/2 – 20 UNF 2 A (e.g. SKR 130/12 UNF),
SKR 240/12 UNF with 3/4 – 16 UNF 2 A thread

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

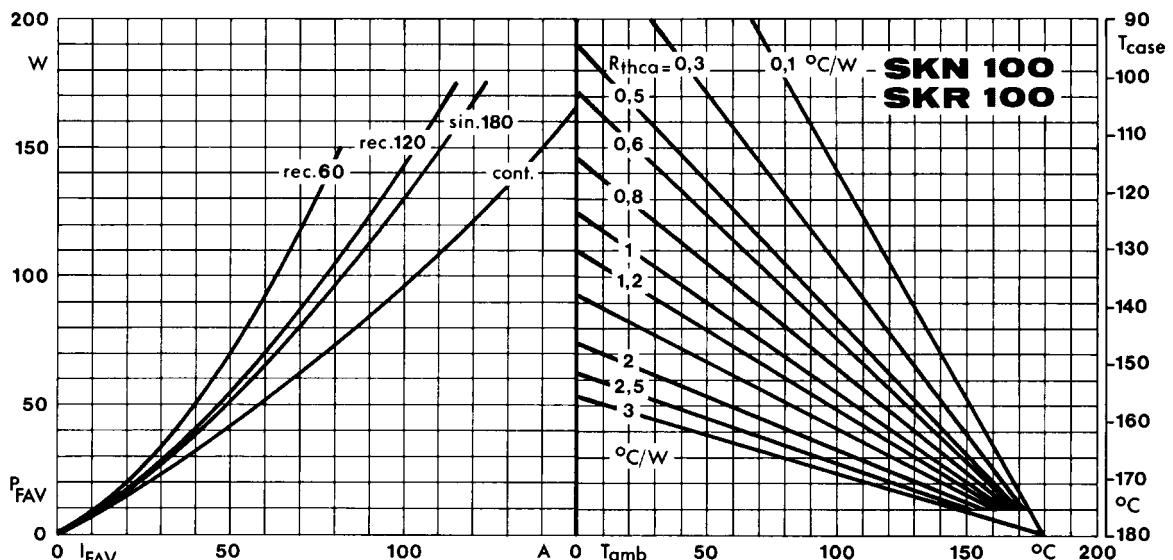


Fig. 1 a Power dissipation vs. forward current and case temperature

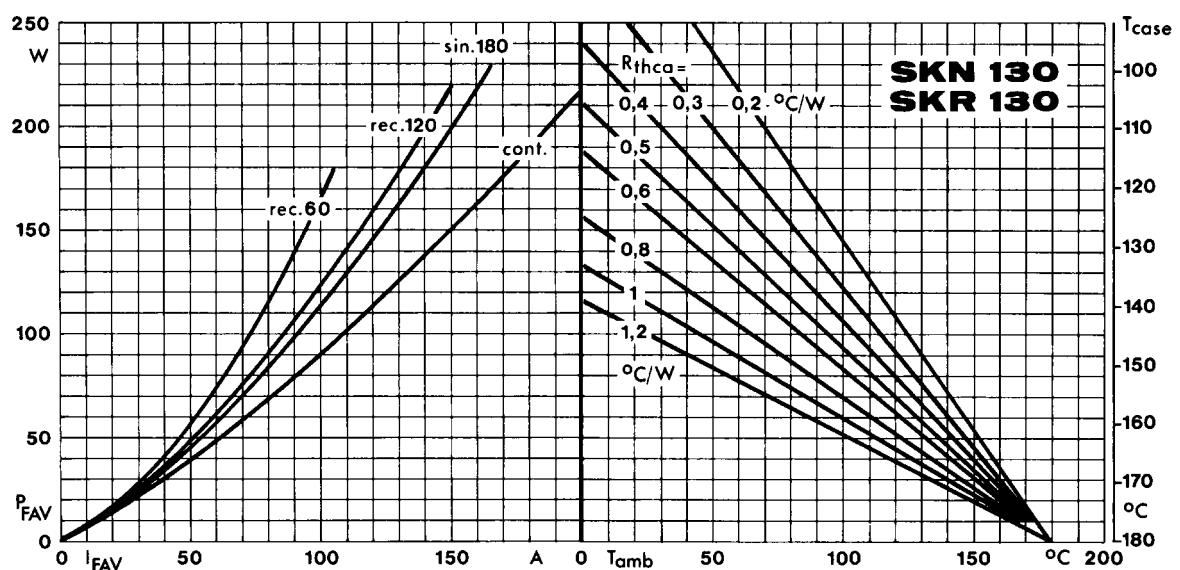


Fig. 1 b Power dissipation vs. forward current and case temperature

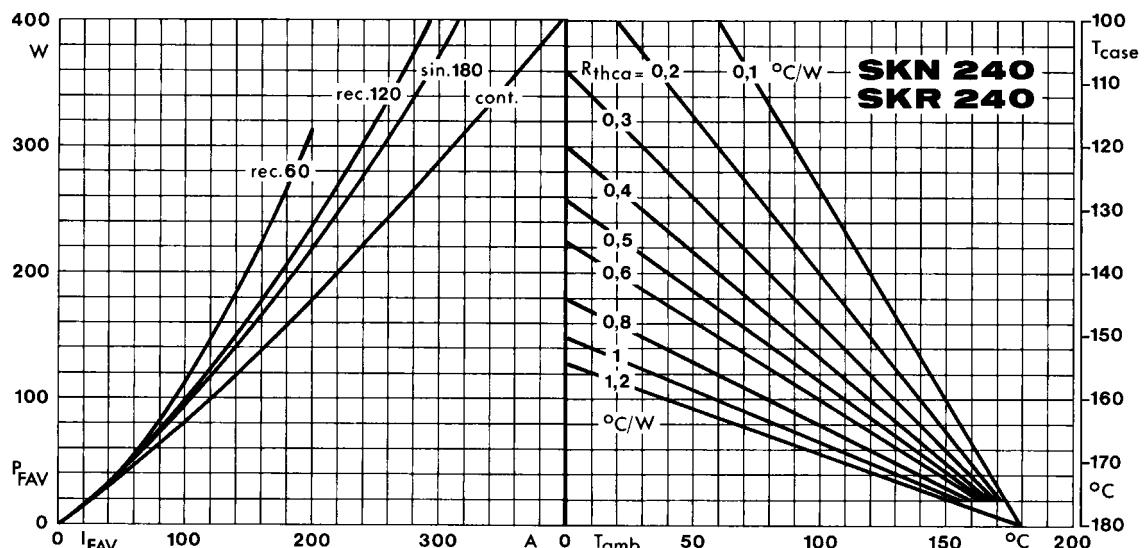


Fig. 1 c Power dissipation vs. forward current and case temperature

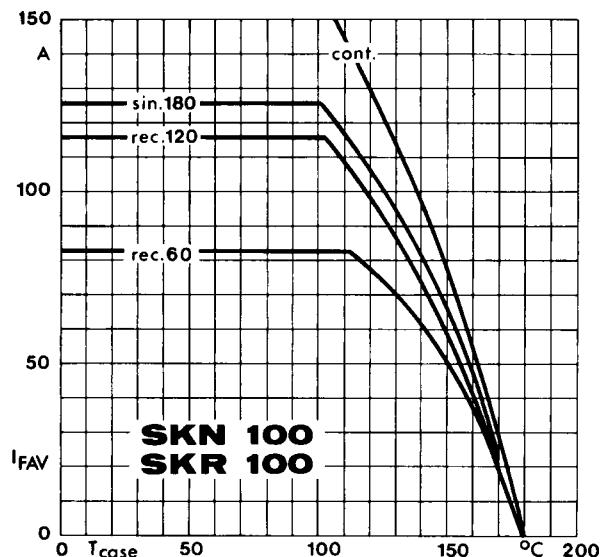


Fig. 3 a Rated forward current vs. case temperature

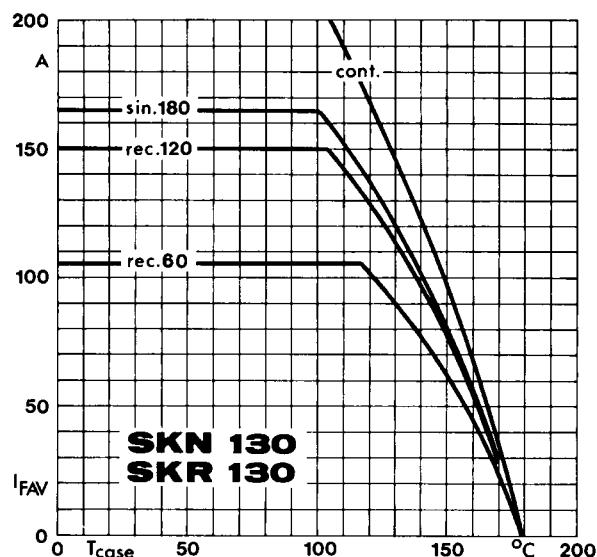


Fig. 3 b Rated forward current vs. case temperature

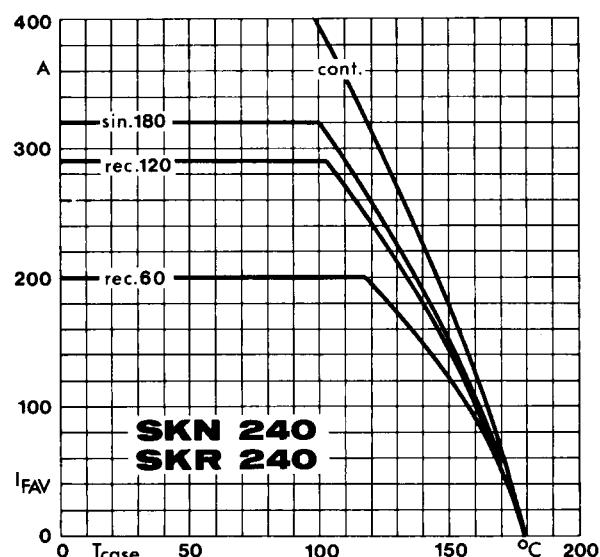


Fig. 3 c Rated forward current vs. case temperature

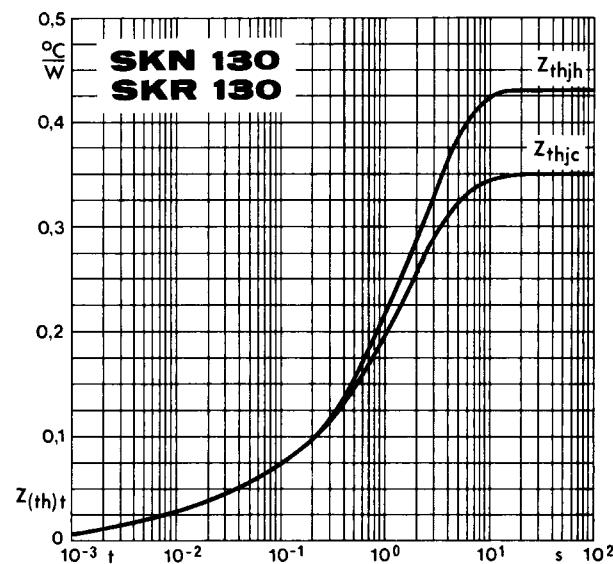


Fig. 5 b Transient thermal impedance vs. time

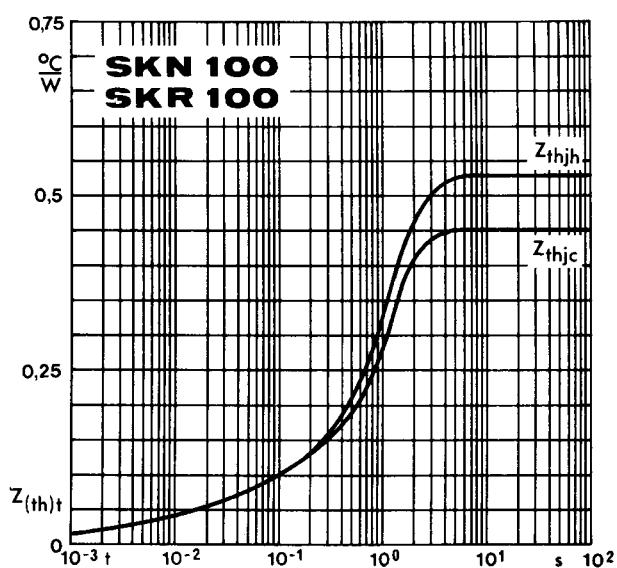


Fig. 5 a Transient thermal impedance vs. time

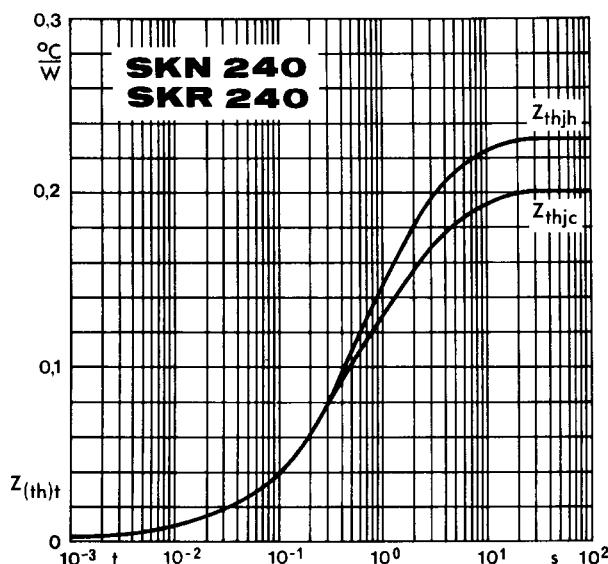


Fig. 5 c Transient thermal impedance vs. time

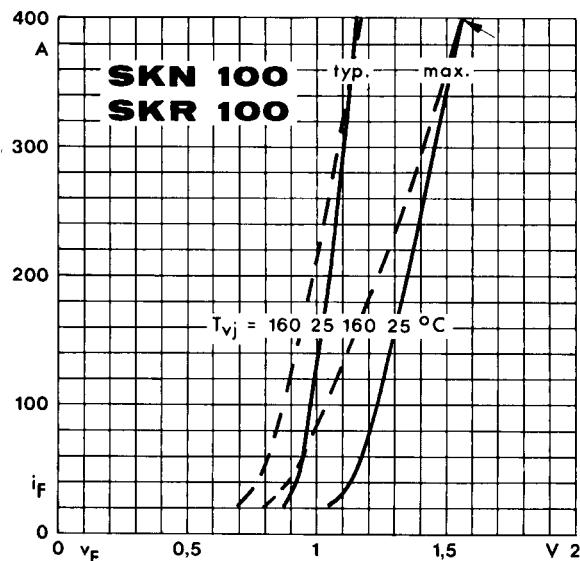


Fig. 6 a Forward characteristics

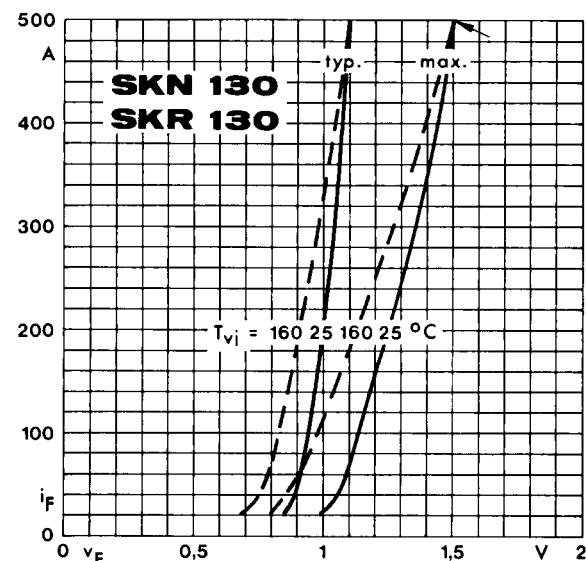


Fig. 6 b Forward characteristics

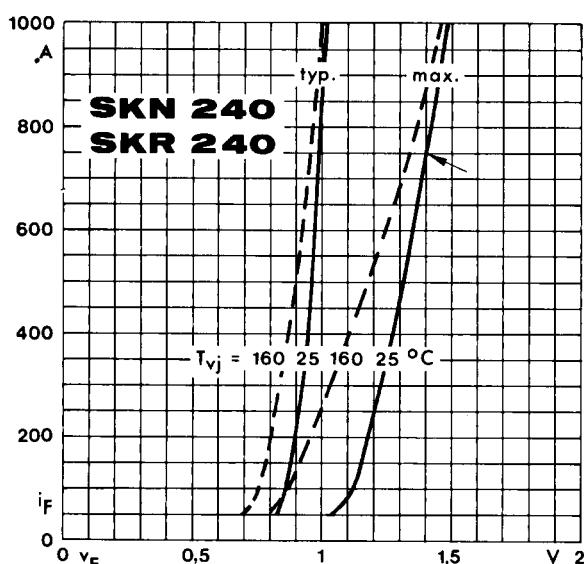


Fig. 6 c Forward characteristics

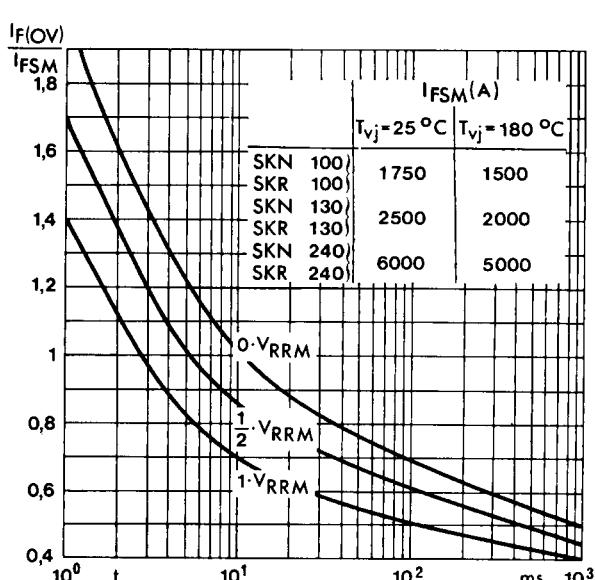
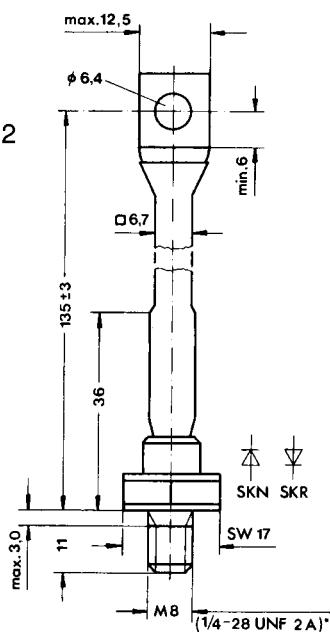


Fig. 7 Surge overload current vs. time

**SKN 45, SKR 45
SKN 70, SKR 70**

Case E 12

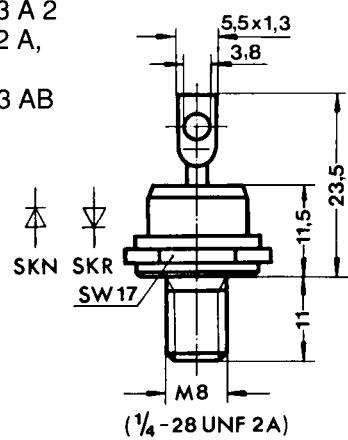
IEC: A 16 U; A 17 M B 2
DIN 41 886: 103 A 2
BS 3934: SO-32 A,
SO-32 B



**SKN 71
SKR 71**

Case E 11

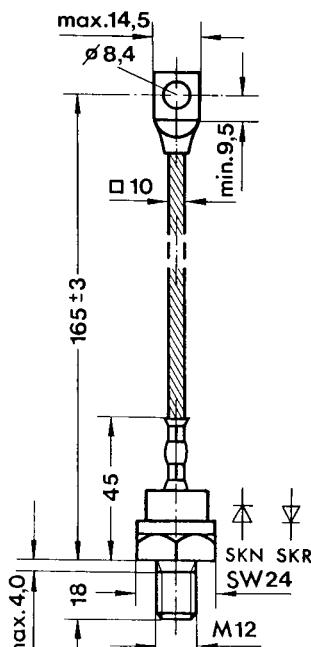
IEC: A 16 U; A 17 M B 2
DIN 41 886: 103 A 2
BS 3934: SO-32 A,
SO-32 B
JEDEC: DO-203 AB
(DO-5)



**SKN 100
SKR 100**

Case E 13

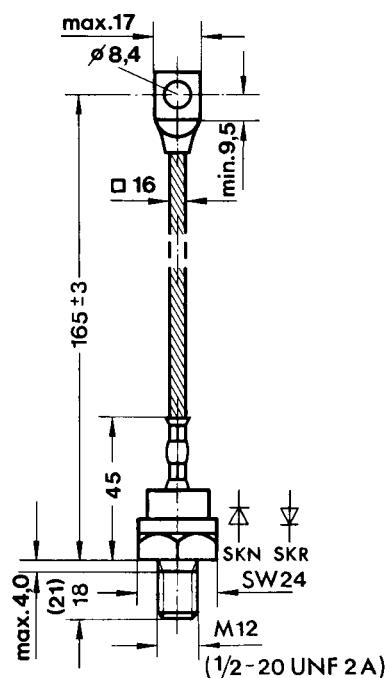
IEC: A 9 MA¹⁾
DIN 41 887: 105 B 2¹⁾
BS 3934: SO-29 B
JEDEC: DO-205 AC



**SKN 130
SKR 130**

Case E 14

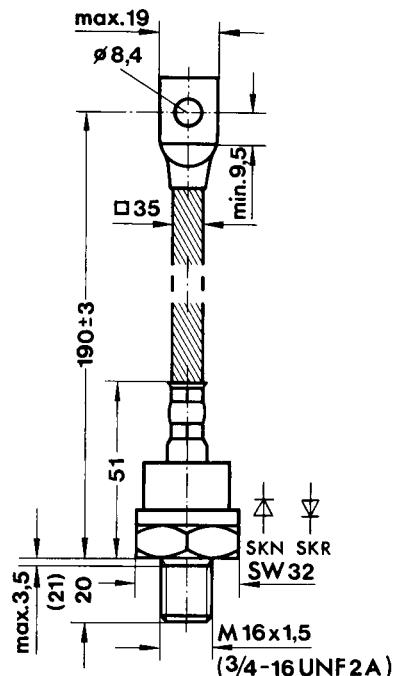
IEC: A 9 MA¹⁾
DIN 41 887: 105 B 2¹⁾
BS 3934: SO-29 B
JEDEC: DO-205 AC
(DO-30)²⁾



**SKN 240
SKR 240**

Case E 15

IEC: A 15 M
DIN 41 887: 106 B 2
BS 3934: SO-42
JEDEC: DO-205 AB
(DO-9)



¹⁾ modified

²⁾ available with thread 1/2-20 UNF 2 A or 3/8-28 UNF 2 A

Dimensions in mm